SPP3052
P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP3052 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, such as DC/DC converter and Desktop computer power management.

The package is universally preferred for commercial industrial surface mount applications

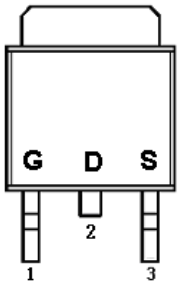
APPLICATIONS

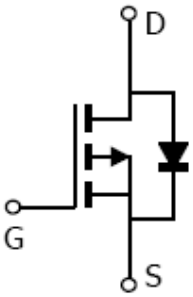
- Power Management in Desktop Computer
- DC/DC Converter
- LCD Display inverter

FEATURES

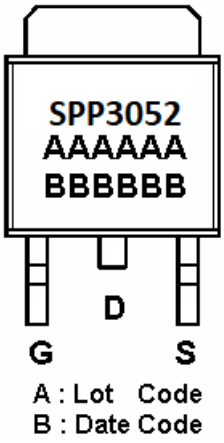
- -30V/- 25A,$R_{DS(ON)}$=50mΩ@V_{GS}=-10V
- -30V/- 16A,$R_{DS(ON)}$=85mΩ@V_{GS}=-4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-252-2L package design

PIN CONFIGURATION (TO-252-2L)





PART MARKING



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P-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3052T252RGB	TO-252-2L	SPP3052

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPP3052T252RGB : Tape Reel ; Pb – Free ; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-25	A
	T_A=70℃		-18	
Pulsed Drain Current		I_{DM}	-100	A
Continuous Source Current(Diode Conduction)		I_S	-2.3	A
Power Dissipation	T_A=25℃	P_D	2.8	W
	T_A=70℃		1.8	
Avalanche Energy with Single Pulse (Tj=25℃, L = 0.14mH , I_{AS} = 43A , V_{DD} = 20V.)		E_{AS}	129	mJ
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	105	℃/W

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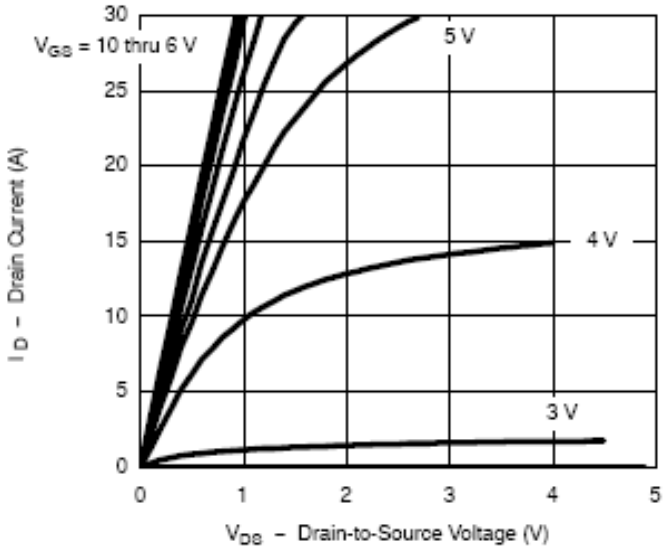
ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

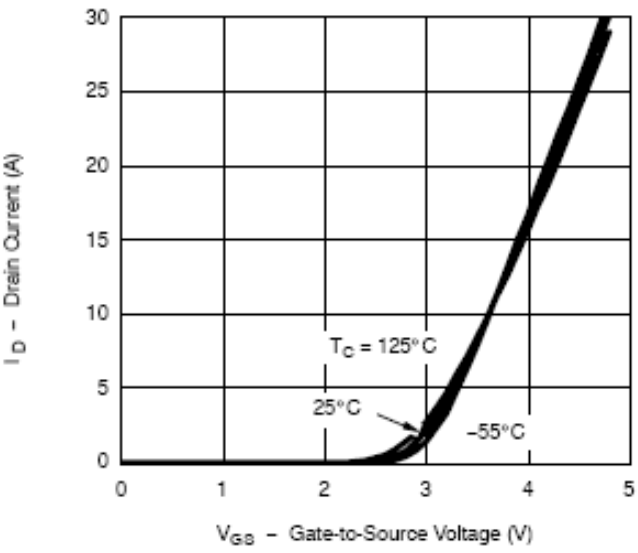
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-1.0		-3.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-21V,V_{GS}=0V			-2	uA
		V_{DS}=-21V,V_{GS}=0V T_J=55℃			-5	
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-25A		0.040	0.050	Ω
		V_{GS}=-5V,I_D=-16A		0.068	0.085	
Forward Transconductance	gfs	V_{DS}=-10V,I_D=-8A		8		S
Diode Forward Voltage	V_{SD}	I_S=-16A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-10V I_D=-3.5A		16	24	nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			4.5		
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V f=1MHz		680		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			75		
Turn-On Time	$t_{d(on)}$	V_{DD}=-15V,R_L=15Ω I_D=-1.0A,V_{GEN}=-10V R_G=6Ω		14	25	nS
	t_r			15	26	
Turn-Off Time	$t_{d(off)}$			42	70	
	t_f			30	50	

TYPICAL CHARACTERISTICS

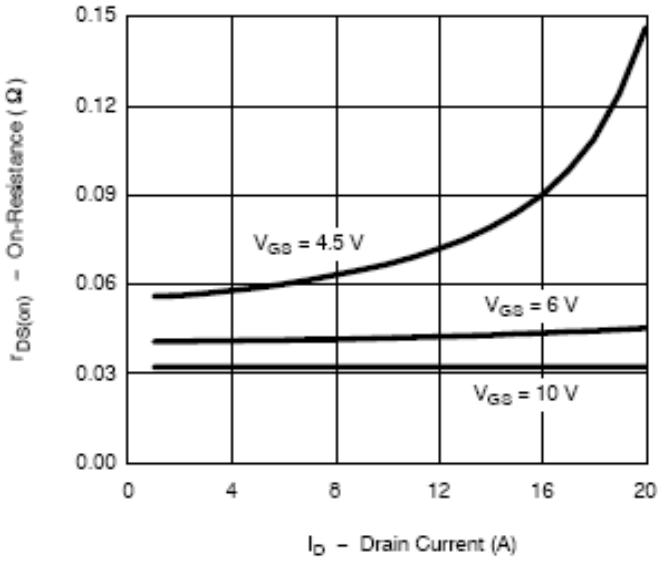
Output Characteristics



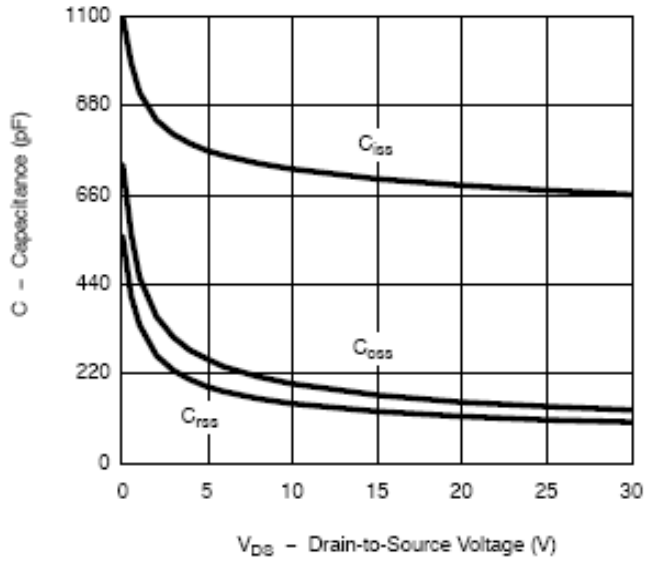
Transfer Characteristics



On-Resistance vs. Drain Current

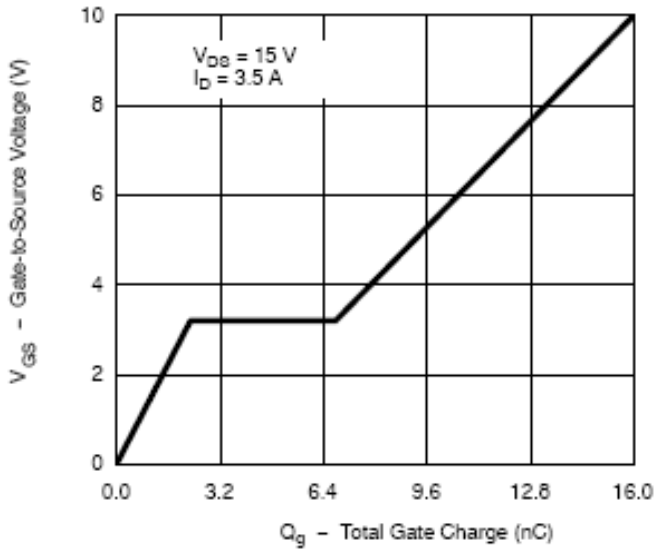


Capacitance

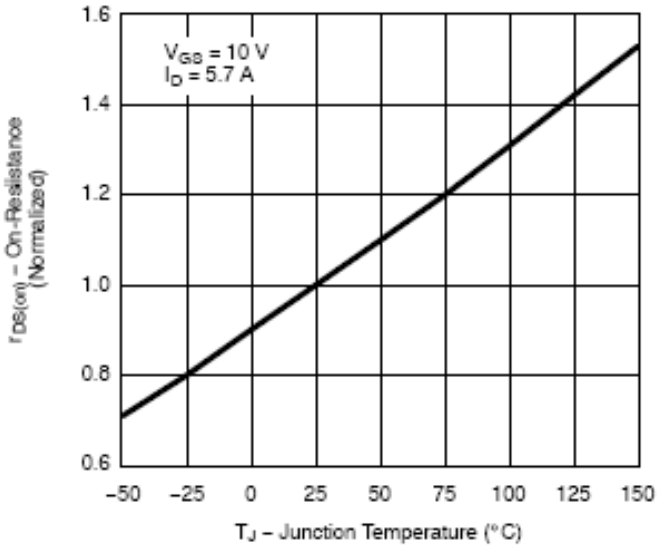


TYPICAL CHARACTERISTICS

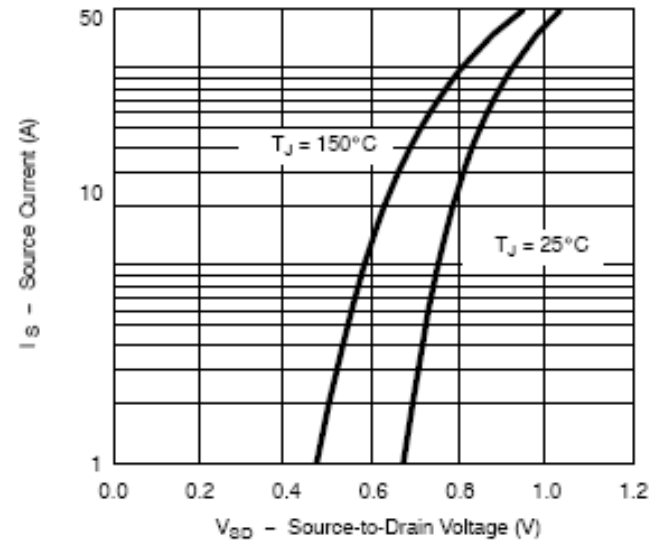
Gate Charge



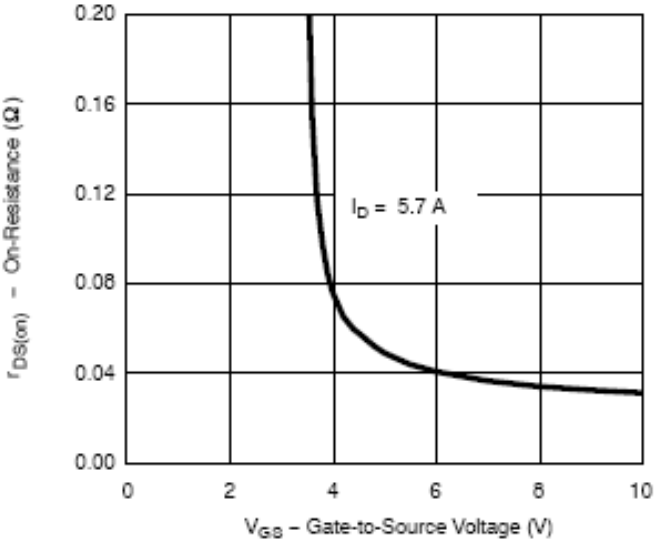
On-Resistance vs. Junction Temperature



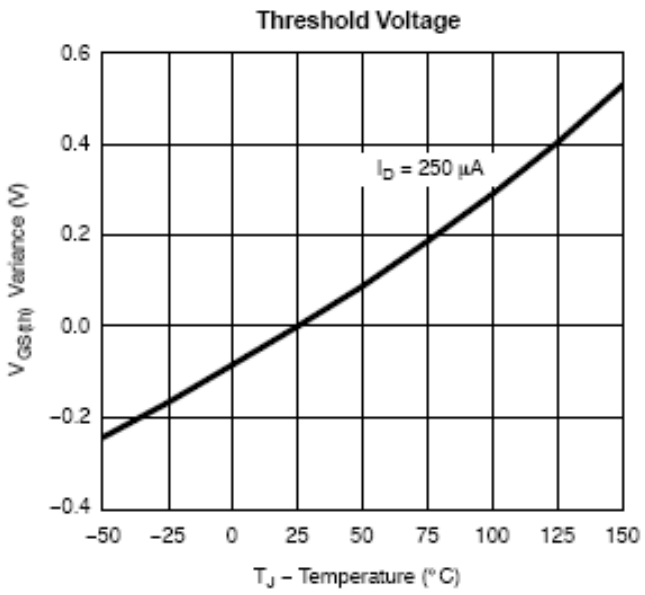
Source-Drain Diode Forward Voltage

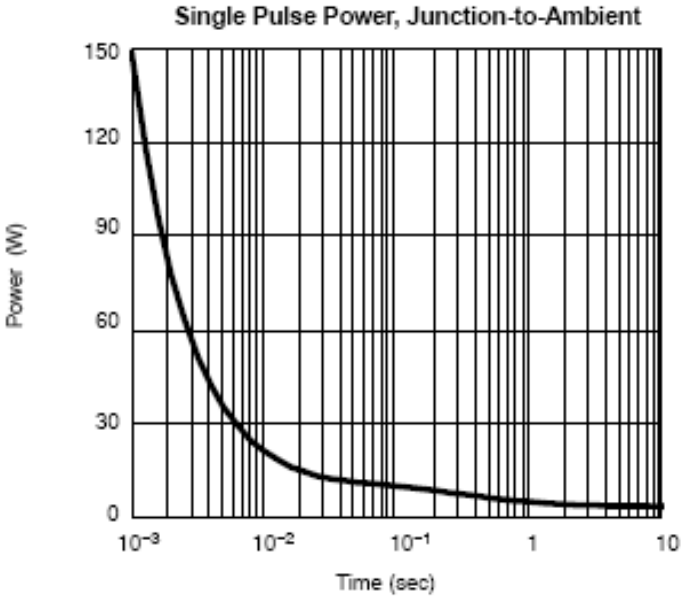


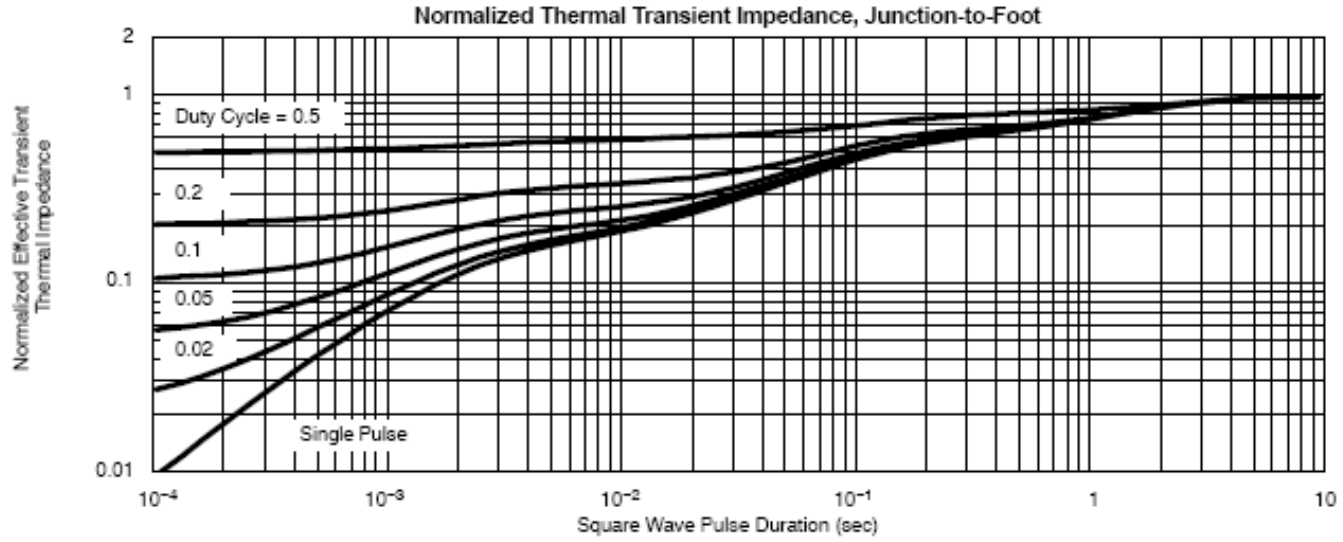
On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS







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